

ZXTDAM832

MPPS™ Miniature Package Power Solutions DUAL 15V NPN LOW SATURATION SWITCHING TRANSISTOR

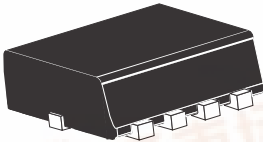
SUMMARY
 $V_{CE0}=15V$; $R_{SAT} = 45m\Omega$; $I_C= 4.5A$

DESCRIPTION

Packaged in the innovative 3mm x 2mm MLP (Micro Leaded Package) outline, these new 4th generation low saturation dual transistors offer extremely low on state losses making them ideal for use in DC-DC circuits and various driving and power management functions.

Additionally users gain several other **key benefits**:

- Performance capability equivalent to much larger packages
- Improved circuit efficiency & power levels
- PCB area and device placement savings
- Lower package height (nom. 0.9mm)
- Reduced component count



3mm x 2mm (Dual die) MLP

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage (100mV @1A)
- h_{FE} characterised up to 12A
- $I_C= 4.5A$ Continuous Collector Current
- 3mm x 2mm MLP

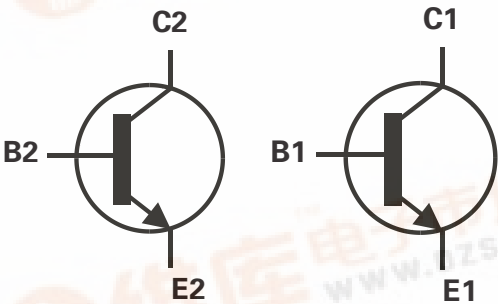
APPLICATIONS

- DC - DC Converters (FET Drivers)
- Charging circuits
- Power switches
- Motor control

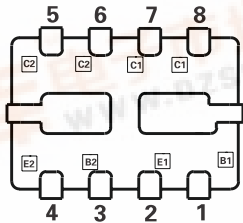
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXTDAM832TA	7"	8mm	3000
ZXTDAM832TC	13"	8mm	10000

DEVICE MARKING
DAA



PINOUT



3mm x 2mm MLP
underside view



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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	7.5	V
Peak Pulse Current	I_{CM}	15	A
Continuous Collector Current (a)(f)	I_C	4.5	A
Continuous Collector Current (b)(f)	I_C	5.0	A
Base Current	I_B	1000	mA
Power Dissipation at $T_A=25^{\circ}\text{C}$ (a)(f)	P_D	1.5	W
Linear Derating Factor		12	mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (b)(f)	P_D	2.45	W
Linear Derating Factor		19.6	mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (c)(f)	P_D	1	W
Linear Derating Factor		8	mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (d)(f)	P_D	1.13	W
Linear Derating Factor		9	mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (d)(g)	P_D	1.7	W
Linear Derating Factor		13.6	mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (e)(g)	P_D	3	W
Linear Derating Factor		24	mW/ $^{\circ}\text{C}$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^{\circ}\text{C}$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	$R_{\theta JA}$	83.3	$^{\circ}\text{C/W}$
Junction to Ambient (b)(f)	$R_{\theta JA}$	51	$^{\circ}\text{C/W}$
Junction to Ambient (c)(f)	$R_{\theta JA}$	125	$^{\circ}\text{C/W}$
Junction to Ambient (d)(f)	$R_{\theta JA}$	111	$^{\circ}\text{C/W}$
Junction to Ambient (d)(g)	$R_{\theta JA}$	73.5	$^{\circ}\text{C/W}$
Junction to Ambient (e)(g)	$R_{\theta JA}$	41.7	$^{\circ}\text{C/W}$

Notes

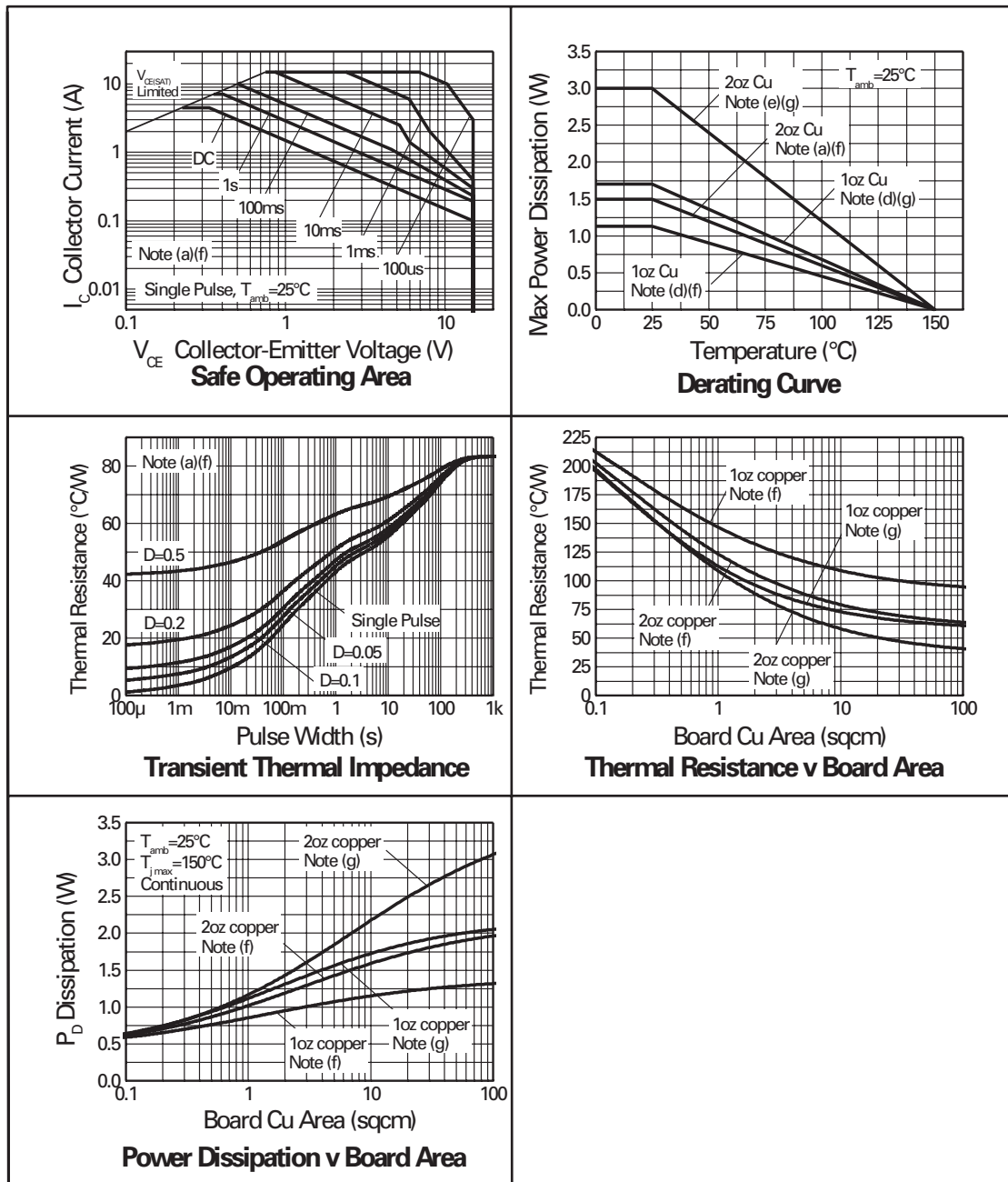
- (a) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (b) Measured at $t < 5$ secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (c) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with minimal lead connections only**.
- (d) For a dual device surface mounted on 10 sq cm single sided 1oz copper on FR4 PCB, in still air conditions **with all exposed pads attached attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (e) For a dual device surface mounted on 85 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (f) For a dual device with one active die.
- (g) For dual device with 2 active die running at equal power.
- (h) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.
- (i) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper 1 oz weight, 1mm wide tracks and one half of the device active is $R_{\theta h} = 250^{\circ}\text{C/W}$ giving a power rating of $P_{tot} = 500\text{mW}$.



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TYPICAL CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	70		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	15	18		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7.5	8.2		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			25	nA	$V_{CB}=32\text{V}$
Emitter Cut-Off Current	I_{EBO}			25	nA	$V_{EB}=6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			25	nA	$V_{CES}=12\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		8	14	mV	$I_C=0.1\text{A}, I_B=10\text{mA}^*$
			70	100	mV	$I_C=1\text{A}, I_B=10\text{mA}^*$
			165	200	mV	$I_C=3\text{A}, I_B=50\text{mA}^*$
			240	280	mV	$I_C=4.5\text{A}, I_B=50\text{mA}^*$
			200		mV	$I_C=4.5\text{A}, I_B=100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.94	1.00	V	$I_C=4.5\text{A}, I_B=50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.88	0.95	V	$I_C=4.5\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200	415			$I_C=10\text{mA}, V_{CE}=2\text{V}^*$
		300	450			$I_C=0.2\text{A}, V_{CE}=2\text{V}^*$
		200	320			$I_C=3\text{A}, V_{CE}=2\text{V}^*$
		150	240			$I_C=5\text{A}, V_{CE}=2\text{V}^*$
			80			$I_C=12\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	80	120		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		30	40	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		120		ns	$V_{CC}=10\text{V}, I_C=1\text{A}$
Turn-Off Time	$t_{(off)}$		160		ns	$I_{B1}=I_{B2}=10\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

